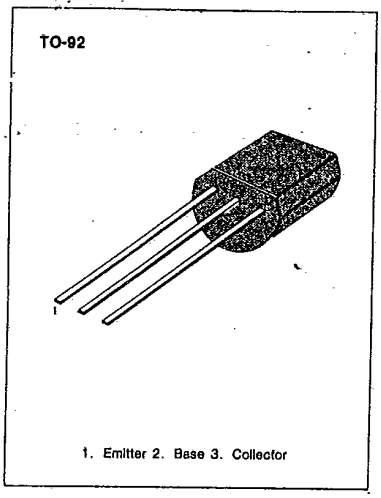
MPS6520 NPN EPITAXIAL SILICON TRANSISTOR

T-29-21

AMPLIFIER TRANSISTOR

- **Collector-Emitter Voltage: V_{CEO}=25V**
- **Collector Dissipation: P_C (max)=625mW**



1. Emitter 2. Base 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	−55~150	°C

* Refer to 2N3904 for graphs

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ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=0.5mA, I_B=0	25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=10μA, I_C=0	4			V
Collector Cut-off Current	I_{CBO}	V_{CB}=30V, I_E=0			50	nA
		V_{CB}=20V, I_E=0			50	nA
DC Current Gain	h_{FE}	I_C=100μA, V_{CE}=10V	100			
		I_C=2mA, V_{CE}=10V	200		400	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=50mA, I_B=5mA			0.5	V
Output Capacitance	Cob	V_{CB}=10V, I_E=0 f=100KHz			3.5	pF
Noise Figure	NF	I_C=10μA, V_{CE}=5V R_S=10KΩ f=10Hz to 10KHz			3	dB